TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VHC374F,TC74VHC374FT,TC74VHC374FK

Octal D-Type Flip Flop with 3-State Output

The TC74VHC374 is an advanced high speed CMOS OCTAL FLIP-FLOP with 3-STATE OUTPUT fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

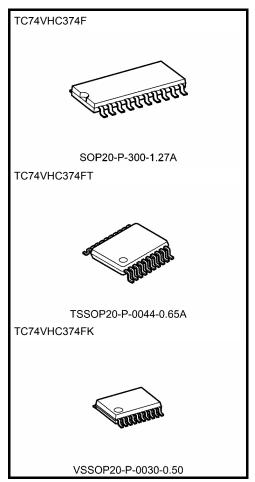
This 8-bit D-type flip-flop is controlled by a clock input (CK) and an output enable input (\overline{OE}).

When the \overline{OE} input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 5.5~V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5~V to 3~V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

Features

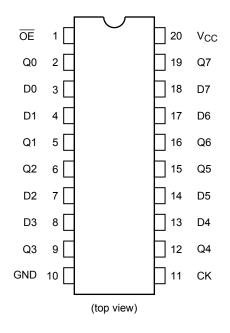
- High speed: $f_{max} = 185 \text{ MHz}$ (typ.) at $V_{CC} = 5 \text{ V}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max)}$ at $T_{a} = 25 \text{°C}$
- High noise immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: $V_{CC \text{ (opr)}} = 2 \text{ to } 5.5 \text{ V}$
- Low noise: VOLP = 0.9 V (max)
- Pin and function compatible with 74ALS374



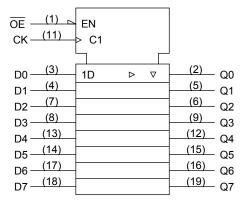
Weight

SOP20-P-300-1.27A : 0.22 g (typ.) TSSOP20-P-0044-0.65A : 0.08 g (typ.) VSSOP20-P-0030-0.50 : 0.03 g (typ.)

Pin Assignment



IEC Logic Symbol



Truth Table

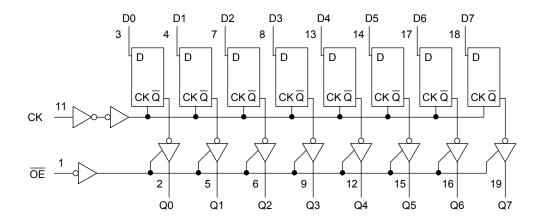
	Inputs	Output	
ŌĒ	CK	D	Output
Н	Х	Χ	Z
L	\neg	Х	Qn
L		L	L
L		Н	Н

X: Don't care

Z: High impedance

Q_n: No change

System Diagram





Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	−0.5 to 7.0	V
DC input voltage	V _{IN}	−0.5 to 7.0	V
DC output voltage	V _{OUT}	-0.5 to V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	Icc	±75	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	−65 to 150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2.0 to 5.5	V	
Input voltage	V_{IN}	0 to 5.5	>	
Output voltage	V _{OUT}	0 to V _{CC}	V	
Operating temperature	T _{opr}	−40 to 85	°C	
Input rise and fall time	dt/dv	0 to 100 (V _{CC} = 3.3 ± 0.3 V)	ns/V	
input rise and fail tille	ui/uv	0 to 20 (V _{CC} = 5 ± 0.5 V)	ns/V	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either V_{CC} or GND.

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Electrical Characteristics

DC Characteristics

Characteristics	Symbol		Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
		V		V _{CC} (V)	Min	Тур.	Max	Min	Max	
High-level input voltage	V _{IH}	_		2.0 3.0 to 5.5	1.50 V _{CC} × 0.7		-	1.50 V _{CC} × 0.7		V
Low-level input voltage	V _{IL}	-		2.0 3.0 to 5.5	_ _	_ _	0.50 V _{CC} × 0.3	_ _	0.50 V _{CC} × 0.3	V
High-level output voltage	V _{ОН}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -50 μA I _{OH} = -4 mA	2.0 3.0 4.5 3.0	1.9 2.9 4.4 2.58	2.0 3.0 4.5	_ _ _	1.9 2.9 4.4 2.48	_ _ _	V
			I _{OH} = −8 mA	4.5	3.94	_	_	3.80	_	
Low-level output voltage	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA I _{OL} = 4 mA I _{OL} = 8 mA	2.0 3.0 4.5 3.0 4.5	_ _ _ _	0.0 0.0 0.0 —	0.1 0.1 0.1 0.36 0.36	- - -	0.1 0.1 0.1 0.44 0.44	٧
3-state output off-state current	I _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	_	_	±0.25	_	±2.50	μА
Input leakage current	I _{IN}	V _{IN} = 5.5 V or GND		0 to 5.5	_	_	±0.1	_	±1.0	μA
Quiescent supply current	Icc	V _{IN} = V _{CC} or	r GND	5.5	_	_	4.0	_	40.0	μΑ

Timing Requirements (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Test Condition		25°C	Ta = -40 to 85°C	Unit
			V _{CC} (V)	Тур.	Limit	Limit	
Minimum pulse width	t _{w (H)}		3.3 ± 0.3	_	5.0	5.5	20
(CK)	t _{w (L)}	_	5.0 ± 0.5	_	5.0	5.0	ns
Minimum set-up time	t _s	1	3.3 ± 0.3	_	4.5	4.5	ns
			5.0 ± 0.5	_	3.0	3.0	115
Minimum hold time	t _h	_	3.3 ± 0.3	_	2.0	2.0	20
			5.0 ± 0.5	_	2.0	2.0	ns



AC Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Tes	Test Condition		Ta = 25°C			Ta = -40 to 85°C		Unit
	- ,		V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	
			3.3 ± 0.3	15	_	8.1	12.7	1.0	15.0	- ns
Propagation delay time	t_{pLH}		3.3 ± 0.3	50	_	10.6	16.2	1.0	18.5	
(CK-Q)	t_{pHL}	_	5.0 ± 0.5	15	1	5.4	8.1	1.0	9.5	
			3.0 ± 0.5	50	1	6.9	10.1	1.0	11.5	
			3.3 ± 0.3	15	1	7.1	11.0	1.0	13.0	
3-state output enable	t_{pZL}	R _L = 1 kΩ	3.5 1 0.5	50	1	9.6	14.5	1.0	16.5	ns
time	t_{pZH}	KL - 1 K12	5.0 ± 0.5	15	1	5.1	7.6	1.0	9.0	
				50	1	6.6	9.6	1.0	11.0	
3-state output disable	t_{pLZ}	R _L = 1 kΩ	3.3 ± 0.3	50	1	10.2	14.0	1.0	16.0	ns
time	t_{pHZ}		5.0 ± 0.5	50	1	6.1	8.8	1.0	10.0	
	£		3.3 ± 0.3	15	80	130	_	70	_	- MHz
Maximum clock				50	55	85	_	50	_	
frequency	f _{max}	_	5.0 ± 0.5	15	130	185	-	110	_	
				50	85	120	-	75	_	
Output to output skew	t _{osLH}	(Note 1)	3.3 ± 0.3	50	1	_	1.5	I	1.5	ns
Output to output skew	t_{osHL}	(Note 1)	5.0 ± 0.5	50	_	_	1.0	_	1.0	113
Input capacitance	C _{IN}		_		_	4	10	-	10	pF
Output capacitance	C _{OUT}				_	6	_	-	_	pF
Power dissipation capacitance	C _{PD}			(Note 2)	-	32		-	_	pF

Note 1: Parameter guaranteed by design.

 $t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|$

Note 2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

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Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 (per F/F)$$

And the total CPD when n pcs. of latch operate can be gained by the following equation:

 C_{PD} (total) = 20 + 12·n

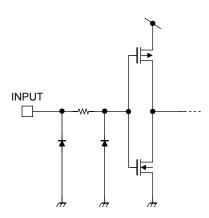


Noise Characteristics (input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Ta =	Unit		
Characteristics	Symbol		V _{CC} (V)	Тур.	Max	Offic
Quiet output maximum dynamic V _{OL}	V_{OLP}	C _L = 50 pF	5.0	0.5	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.5	-0.8	V
Minimum high level dynamic input voltage	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

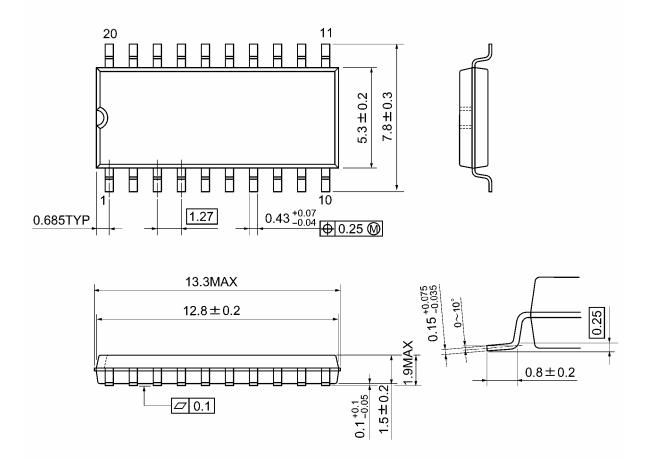
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Input Equivalent Circuit



Package Dimensions

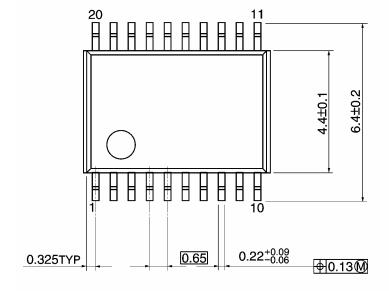
SOP20-P-300-1.27A Unit: mm

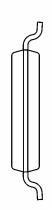


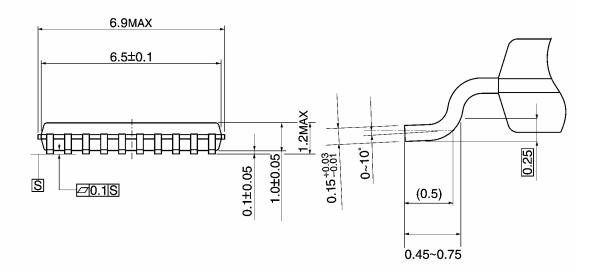
Weight: 0.22 g (typ.)

Package Dimensions

TSSOP20-P-0044-0.65A Unit: mm





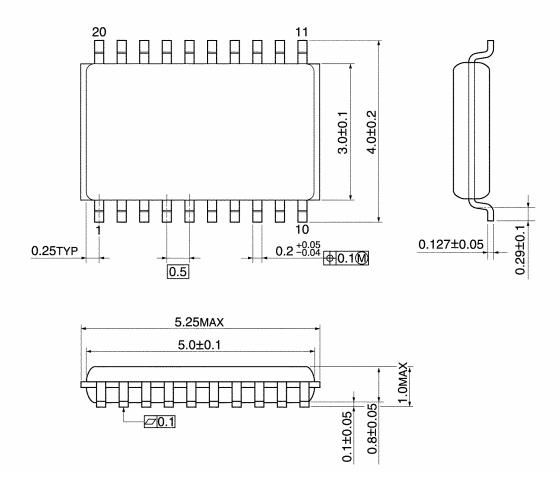


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Weight: 0.08 g (typ.)

Package Dimensions

VSSOP20-P-0030-0.50 Unit: mm



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Weight: 0.03 g (typ.)

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20070701-EN GENERAL

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